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Shin

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(54) **ORGANIC LIGHT EMITTING DIODE
DISPLAY HAVING IMPROVED STRENGTH
BY PREVENTING THE EXFOLIATION OF A
SEALANT**

(58) **Field of Classification Search**
USPC 313/498–512; 257/40, 98–99
See application file for complete search history.

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patent is extended or adjusted under 35
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(62) Division of application No. 12/470,013, filed on May
21, 2009, now Pat. No. 8,378,569.

(57) **ABSTRACT**

(30) **Foreign Application Priority Data**

Nov. 5, 2008 (KR) 10-2008-0109449

An organic light emitting diode (OLED) display. The OLED display includes a first substrate member, a first conductive wire having a contact region and formed over the first substrate member, an insulating layer including a plurality of wire contact holes exposing a part of the contact region of the first conductive wire and formed over the first conductive wire, a second conductive wire formed over the first conductive wire and connected to the first conductive wire through the plurality of wire contact holes of the insulating layer, a sealant formed over the second conductive wire, a sealing member formed over the sealant, and a fill-up layer disposed above or under the contact region of the first conductive wire.

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H01L 51/52 (2006.01)
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2251/562 (2013.01)
USPC **313/501**; 313/506; 313/507

14 Claims, 7 Drawing Sheets

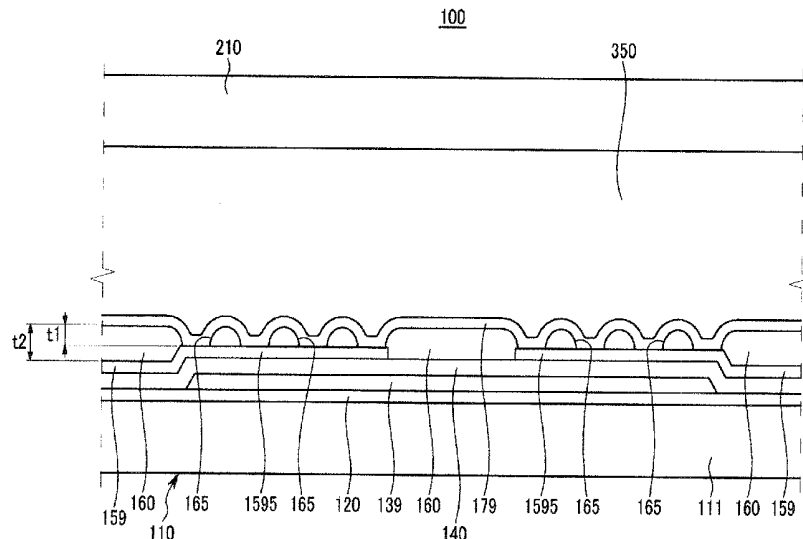


FIG. 1

100

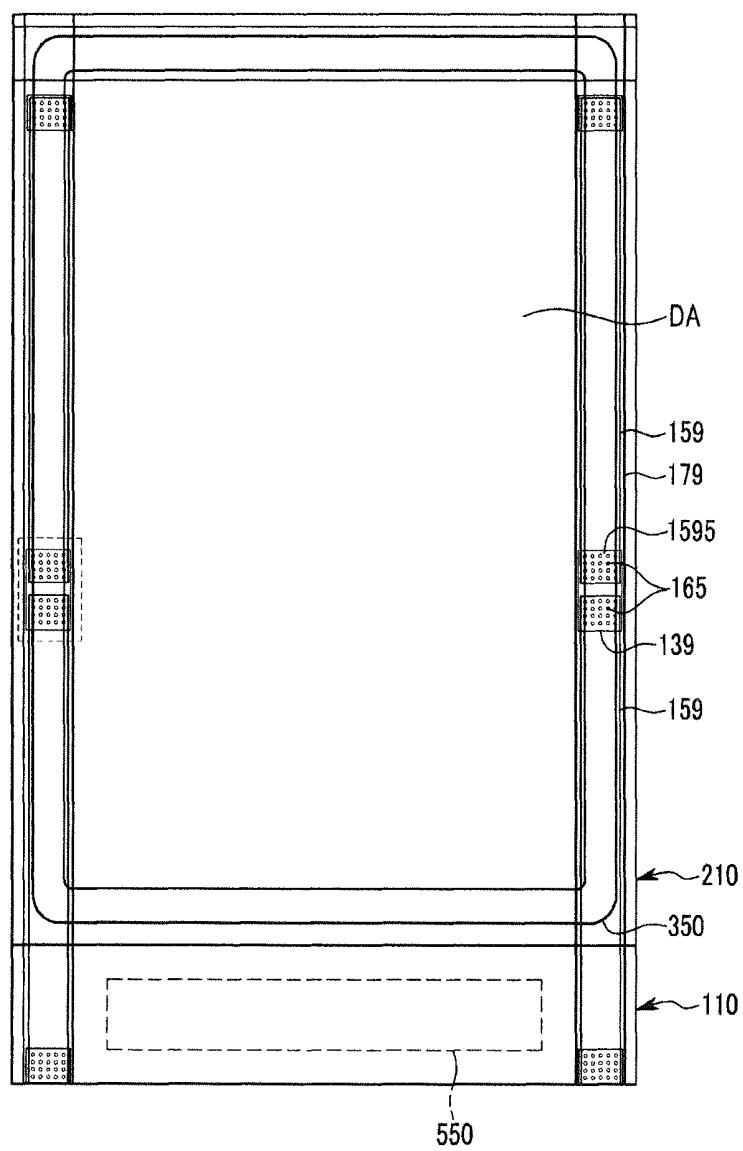


FIG. 2

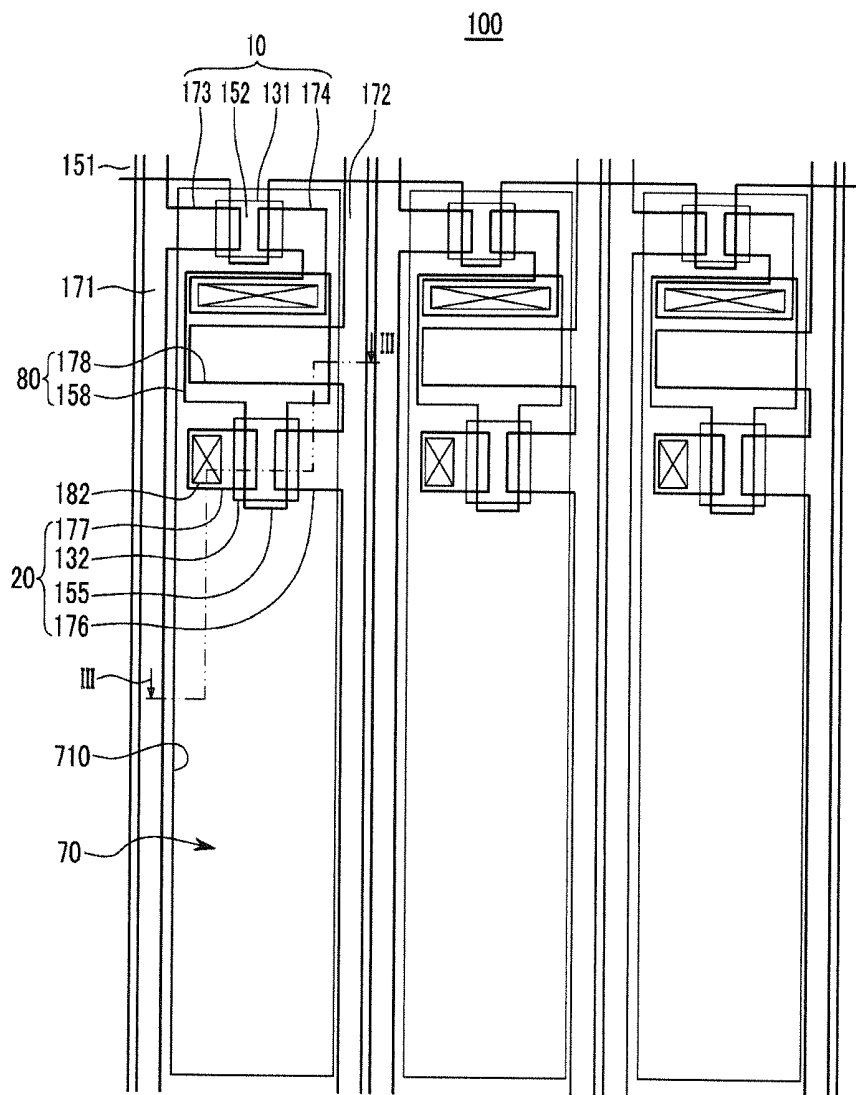


FIG. 3

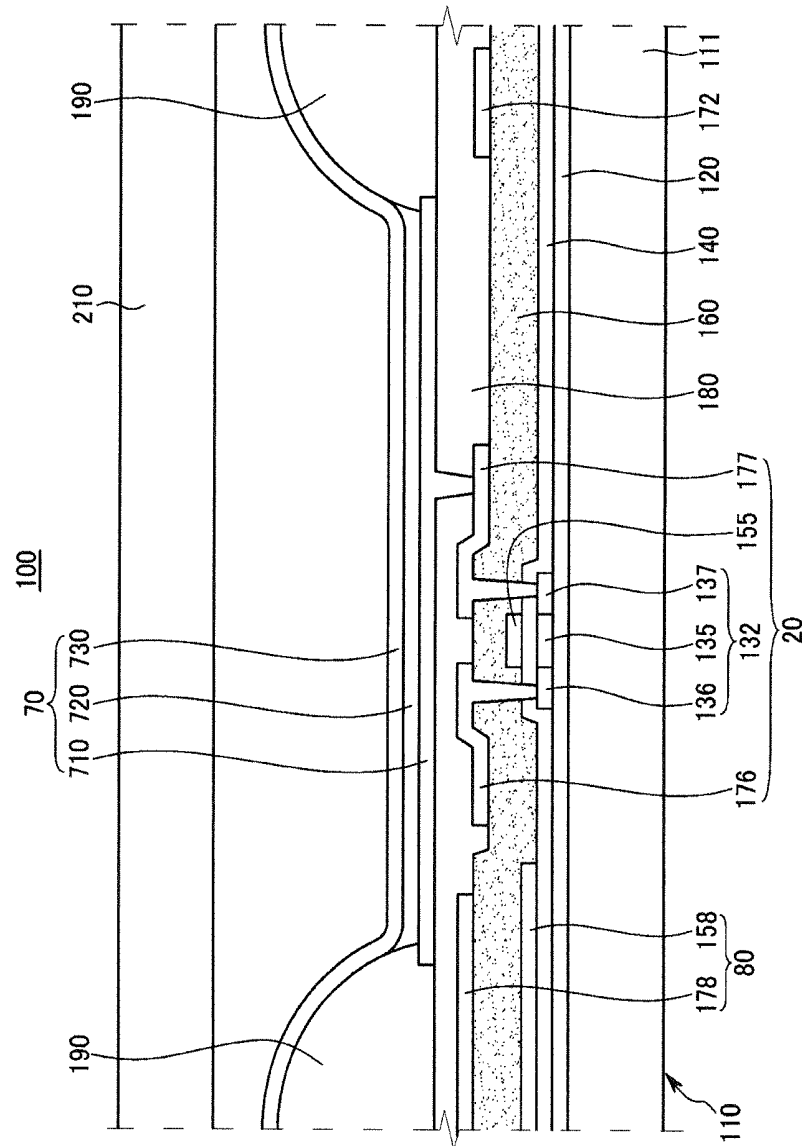


FIG. 4

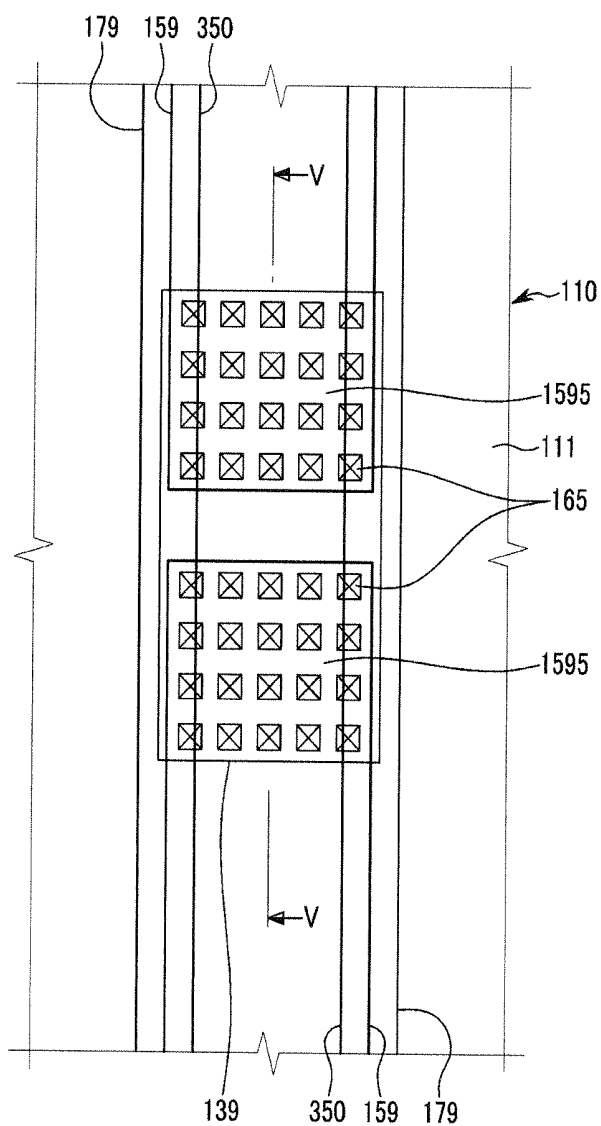


FIG. 5

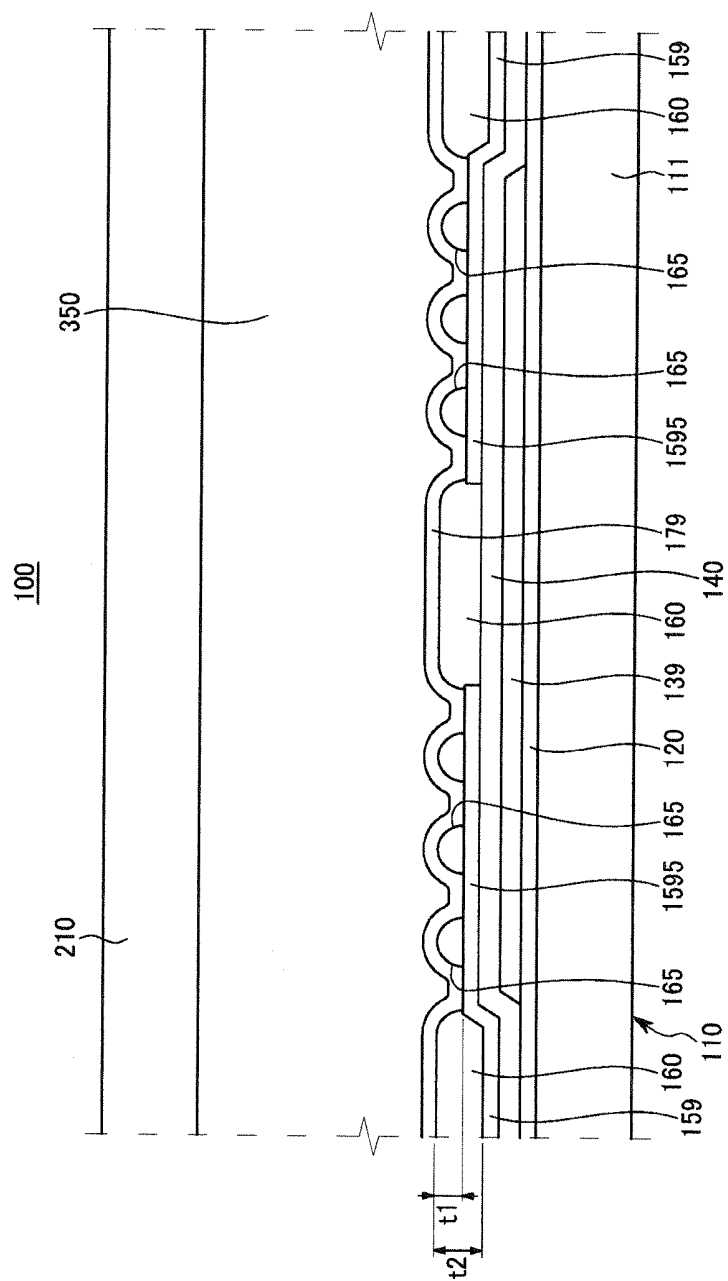


FIG. 6

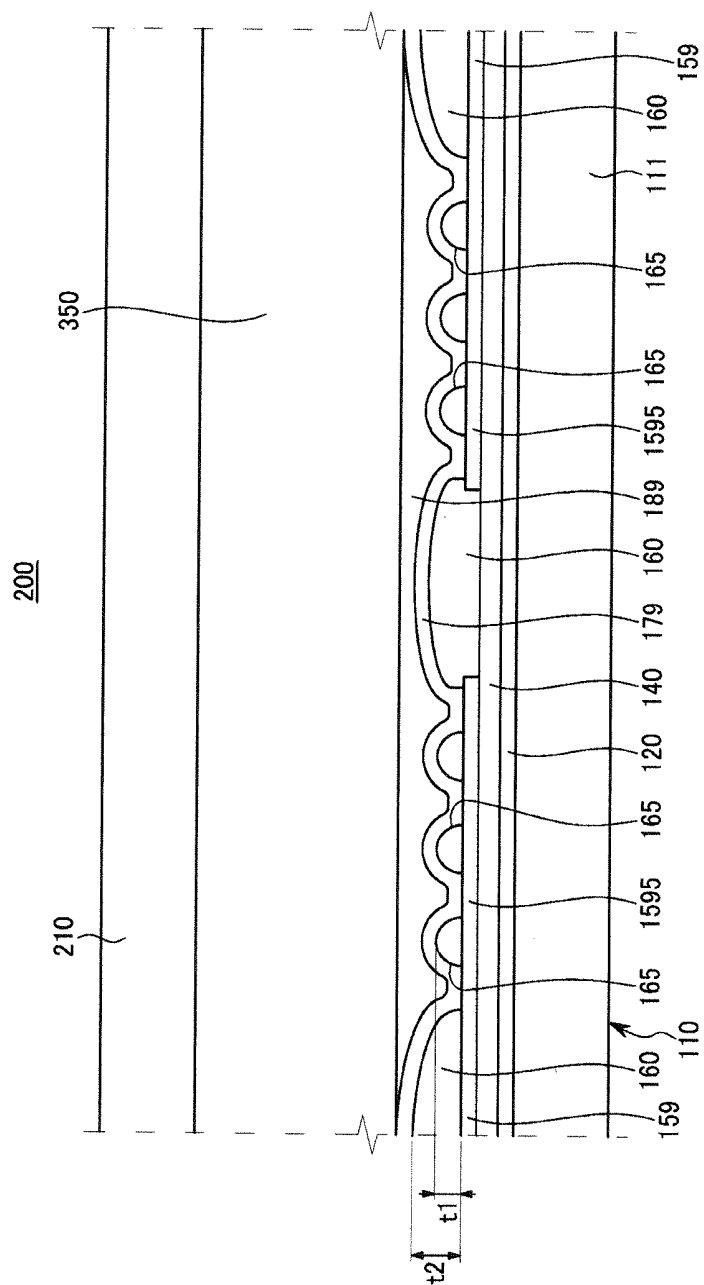
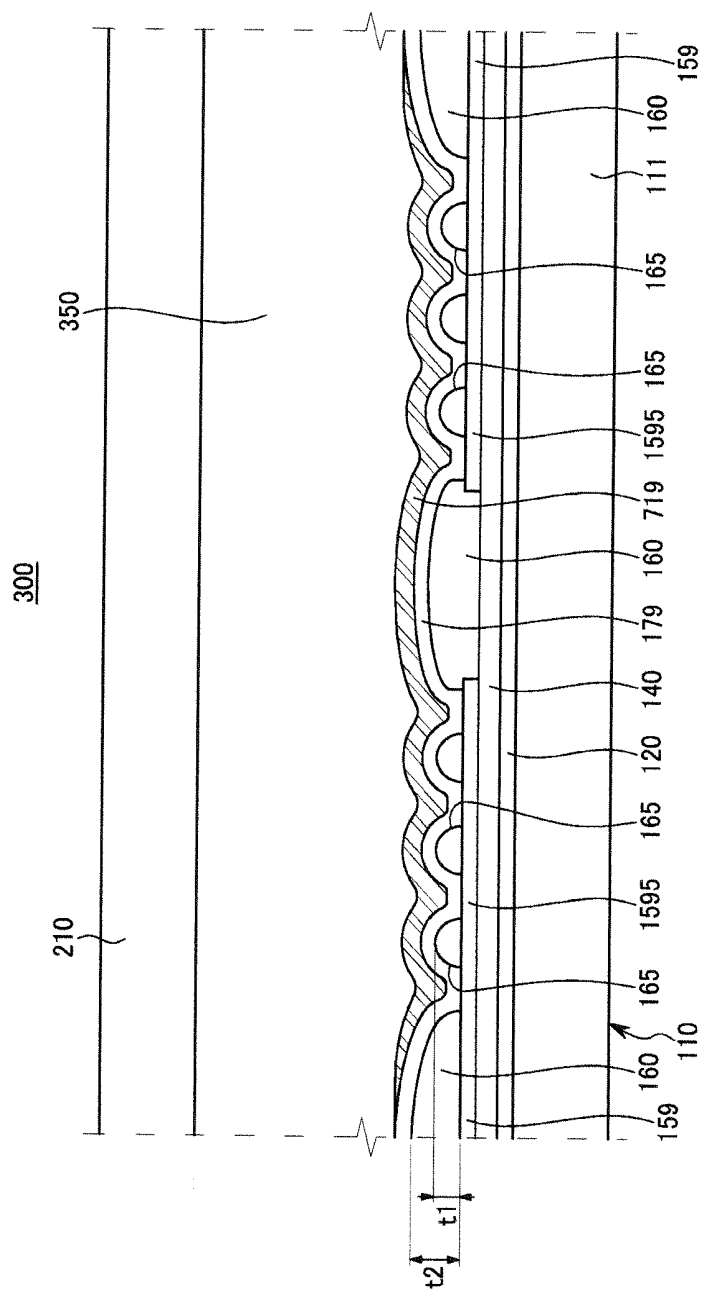


FIG. 7



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ORGANIC LIGHT EMITTING DIODE DISPLAY HAVING IMPROVED STRENGTH BY PREVENTING THE EXFOLIATION OF A SEALANT

CROSS-REFERENCE TO RELATED APPLICATION

This application claims the benefit of Korean Patent Application No. 2008-109449 filed Nov. 5, 2008, in the Korean Intellectual Property Office, the disclosure of which is incorporated herein by reference. Furthermore, this application is filed pursuant to 35 U.S.C. §121 as a Divisional application of Applicants' patent application Ser. No. 12/470,013 filed in the U.S. Patent & Trademark Office on 21 May 2009 (now U.S. Pat. No. 8,378,569), and assigned to the assignee of the present invention. All benefits accruing under 35 U.S.C. §120 from the aforesaid present application Ser. No. 12/470,013 are also claimed.

BACKGROUND OF THE INVENTION

1. Field of the Invention

Aspects of the present invention relate to an organic light emitting diode (OLED) display. More particularly, aspects of the present invention relate to an organic light emitting diode (OLED) display with improved strength.

2. Description of the Related Art

An organic light emitting diode (OLED) display has a self-emissive characteristic and does not require an additional light source, unlike a liquid crystal display. Therefore, the OLED display can be reduced in thickness and weight. Also, the OLED display has been receiving attention as a next generation portable display device because the OLED display has high definition characteristics and low power consumption, high luminance, and fast reaction speed.

In general, a mother panel of an OLED display is initially manufactured, and then the mother panel is divided into a plurality of OLED displays. An image quality test and an aging process are performed on the mother panel. In order to perform these processes, testing/aging wires are formed along edges of each OLED display.

An OLED display includes a display substrate having thin film transistors and organic light emitting diodes, a sealing member for covering the display substrate, and a sealant for making the display substrate cohere with the sealing member. Here, the sealant is coated along an edge of the sealing member for sealing a space between the display substrate and the sealing member.

Therefore, the testing/aging wires overlap with the sealant at the edge of the OLED. Furthermore, the adhesion of the sealant deteriorates by a step difference generated by the testing/aging wires, and the sealing member may separate from the display substrate in the OLED display.

The above information disclosed in this Background section is only for enhancement of understanding of the background of the invention and therefore it may contain information that does not form the prior art that is already known to a person of ordinary skill in the art.

SUMMARY OF THE INVENTION

Aspects of the present invention provide an organic light emitting diode (OLED) display having improved strength by suppressing exfoliation.

An exemplary embodiment of the present invention provides an organic light emitting diode (OLED) display includ-

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ing a first substrate member, a first conductive wire having a contact region formed over the first substrate member, an insulating layer including a plurality of wire contact holes that expose a part of the contact region of the first conductive wire formed over the first conductive wire, a second conductive wire formed over the first conductive wire connected to the first conductive wire through the plurality of wire contact holes of the insulating layer, a sealant formed over the second conductive wire, a sealing member formed over the sealant, and a fill-up layer disposed above or under the contact region of the first conductive wire.

The insulating layer formed over the contact region may be thinner than an average thickness of the insulating layer.

The first conductive wire may be broken at regular intervals.

The contact region may be at an end of the broken first conductive wire.

The first conductive wire may include at least one metal of chromium (Cr), molybdenum (Mo), titanium (Ti), or tantalum (Ta).

The first conductive wire and the second conductive wire may be formed to be flat.

The fill-up layer may be disposed under the first conductive wire.

The OLED display may further include a thin film transistor having a semiconductor layer, and the fill-up layer may be formed of the same material as that of the semiconductor layer of the thin film transistor through the same manufacturing process.

The fill-up layer may be disposed over the first conductive wire.

The OLED display may further include a thin film transistor, an organic light emitting diode, and a planarization layer disposed between the thin film transistor and the organic light emitting diode. The fill-up layer may be formed of the same material as that of the planarization layer through the same manufacturing process.

The OLED may further include an organic light emitting diode having a first electrode, an organic emission layer formed over the first electrode, and a second electrode formed over the organic emission layer. The fill-up layer may be formed of the same material as that of the first electrode of the organic light emitting diode through the same manufacturing process.

According to aspects of the present invention, the strength of the OLED display can improve by suppressing exfoliation.

Additional aspects and/or advantages of the invention will be set forth in part in the description which follows and, in part, will be obvious from the description, or may be learned by practice of the invention.

BRIEF DESCRIPTION OF THE DRAWINGS

These and/or other aspects and advantages of the invention will become apparent and more readily appreciated from the following description of the embodiments, taken in conjunction with the accompanying drawings of which:

FIG. 1 is a top plan view of an organic light emitting diode (OLED) display according to the first exemplary embodiment of the present invention;

FIG. 2 is a partial magnified layout view of a display area of FIG. 1;

FIG. 3 is a cross-sectional view of FIG. 2 along the line III-III;

FIG. 4 is a partial magnified layout of an area of FIG. 1 having a sealant;

FIG. 5 is a cross-sectional view of FIG. 4 along the line V-V;

FIG. 6 is a partial cross-sectional view of an organic light emitting diode (OLED) display according to the second exemplary embodiment of the present invention; and

FIG. 7 is a partial cross-sectional view of an organic light emitting diode (OLED) display according to the third exemplary embodiment of the present invention.

DETAILED DESCRIPTION OF THE EMBODIMENTS

Reference will now be made in detail to the present embodiments of the present invention, examples of which are illustrated in the accompanying drawings, wherein like reference numerals refer to the like elements throughout. The embodiments are described below in order to explain the present invention by referring to the figures.

In FIGS. 1-7, a size and a thickness of each element is approximately shown for better understanding and ease of description. Therefore, the aspects of the present invention are not limited to the drawings.

In the figures, the thickness of layers, films, panels, regions, etc., are exaggerated for clarity. Like reference numerals designate like elements throughout the specification. As referred to herein, when a first element is said to be disposed or formed "on", or "over", a second element, the first element can directly contact the second element, or can be separated from the second element by one or more other elements located therebetween. In contrast, when an element is referred to as being disposed or formed "directly on" or "directly over" another element, there are no intervening elements present.

To clearly explain aspects of the present invention, portions having no connection to the explanation are omitted, and the same or similar constituent elements are designated by the same reference numerals throughout the specification.

Also, the first exemplary embodiment will be described using like reference numerals for like constituent elements having the same structure in various exemplary embodiments. Other exemplary embodiments will be described based on differences from the first exemplary embodiment.

Although the accompanying drawings illustrate an active matrix (AM) type of OLED display having a 2Tr-1Cap structure in which two thin film transistors (TFT) and one capacitor are disposed in a pixel, aspects of the present invention are not limited thereto. Therefore, the OLED display may have various structures. For example, the OLED display may include three or more thin film transistors and two or more capacitors at one pixel, and may further include additional wires.

Here, the pixel is a minimum unit for displaying an image, and the OLED display displays an image through a plurality of pixels.

Hereinafter, an organic light emitting diode (OLED) display according to the first exemplary embodiment of the present invention will be described with reference to FIG. 1 to FIG. 5.

As shown in FIG. 1, the OLED display 100 according to the first exemplary embodiment of the present invention includes a display substrate 110, a sealing member 210 for covering the display substrate 110, and a sealant 350 disposed between the display substrate 110 and the sealing member 210.

The sealant 350 is disposed along an edge of the sealing member 210 and makes the display substrate 110 cohere with the sealing member 210. Hereinafter, an inner space between the substrate 110 and the sealing member 210 surrounded by

the sealant 350 is referred to as a display area DA. The display area DA includes a plurality of pixels formed therein for displaying images.

The sealing member 210 is formed to have a smaller size than that of the display substrate 110. An integrated circuit chip 550 may be mounted at one edge of the display substrate 110 that is not covered by the sealing member 210.

The display substrate 110 includes a first conductive wire 159 and a second conductive wire 179. The first conductive wire 159 and the second conductive wire 179 are disposed at an edge of the display substrate 110. Therefore, the first conductive wire 159 and the second conductive wire 179 overlap with the sealant 350. The first conductive wire 159 and the second conductive wire 179 may not be elements for driving the OLED display 100 but, rather, may be used for an image quality test and an aging process in a fabricating process of the OLED display 100.

The first conductive wire 159 and the second conductive wire 179 are formed in parallel. In more detail, an interlayer insulating layer 160 (see FIG. 3) is formed over the first conductive wire 159, and the second conductive wire 179 is formed over the interlayer insulating layer 160.

Also, the first conductive wire 159 is broken at regular intervals, and an end of the broken first conductive wire 159 becomes a contact region 1595. The first conductive wire 159 includes at least one metal of chromium (Cr), molybdenum (Mo), titanium (Ti), or tantalum (Ta). The first conductive wire 159 is broken as described above to obtain durability and stability in consideration of characteristics and electrical resistance of a metal used for the first conductive wire 159.

The interlayer insulating layer 160 (see FIG. 3) includes a plurality of wire contact holes 165 that expose a part of the contact region of the first conductive wire 159. The second conductive wire 179 is connected to the first conductive wire 159 through the wire contact holes 165 of the interlayer insulating layer 160. Therefore, the first conductive wire 159, which is broken at predetermined intervals, is electrically connected to the second conductive wire 179.

Also, the display substrate 110 further includes a fill-up layer 139. The fill-up layer 139 is disposed over or under the contact region 1595 of the first conductive wire 159. In the OLED display 100 according to the first exemplary embodiment of the present invention, the fill-up layer 139 is disposed under the contact region 1595 of the first conductive wire 159.

Hereinafter, an internal structure of an OLED display 100 will be described based on a pixel formed in a display area (DA) with reference to FIG. 2 and FIG. 3.

As shown in FIG. 2, the display substrate 110 includes a switching thin film transistor 10, a driving thin film transistor 20, a capacitor 80, and an organic light emitting diode (OLED) 70, which are formed in each of the pixels. The display substrate 110 further includes a gate line 151 disposed in one direction, and a data line 171 and a power line 172, which are insulated from the gate line 151 and cross the gate line 151. Here, one pixel may be defined by boundaries of the gate line 151, the data line 171, and the common power line 172. However, aspects of the present invention are not limited thereto.

The organic light emitting diode 70 includes a first electrode 710, an organic emission layer 720 formed over the first electrode 710, and a second electrode 730 (see FIG. 3) formed over an organic emission layer 720 (see FIG. 3). Here, the first electrode 710 has positive polarity (+) as a hole injection electrode, and the second electrode 730 has negative polarity (-) as an electron injection electrode. However, the first exemplary embodiment of the present invention is not limited thereto. The first electrode 710 may be a cathode and the

second electrode **730** may be an anode according to a driving method of the OLED display **100**. Holes and electrons are injected into the inside of the organic emission layer **720** from the first electrode **710** and the second electrode **730**. Excitons are formed when the injected holes are combined with the injected electrons, and light is emitted when an excited state of the excitons is dropped to a ground state.

As shown in FIG. 3, the capacitor **80** includes a first capacitor plate **158** and a second capacitor plate **178** with a gate insulating layer **140** interposed therebetween. Here, the gate insulating layer **140** is a dielectric material. Capacitance is determined by a charge accumulated in the capacitor **80** and a voltage between the first and second capacitor plates **158** and **178**.

As shown in FIG. 2, the switching thin film transistor **10** includes a switching semiconductor layer **131**, a switching gate electrode **152**, a switching source electrode **173**, and a switching drain electrode **174**. The driving thin film transistor **20** includes a driving semiconductor layer **132**, a driving gate electrode **155**, a driving source electrode **176**, and a driving drain electrode **177**.

The switching thin film transistor **10** is used as a switch for selecting a pixel to emit light. The switching gate electrode **152** is connected to the gate line **151**. The switching source electrode **173** is connected to the data line **171**. The switching drain electrode **174** is separated from the switching source electrode **173** and connected to the first capacitor plate **158**.

The driving thin film transistor **20** applies a driving power to the first electrode **710** for controlling the organic emission layer **720** of the organic light emitting diode **70** in the selected pixel to emit light. The driving gate electrode **155** is connected to the first capacitor plate **158**. The driving source electrode **176** and the second capacitor plate **178** are connected to the common power line **172**, respectively. The driving drain electrode **177** is connected to the first electrode **710** of the organic light emitting diode **70** through the electrode contact hole **182**.

By the described structure, the switching thin film transistor **10** is driven by a gate voltage applied to the gate line **151** and transfers a data voltage applied to the data line **171** to the driving thin film transistor **20**. A voltage corresponding to a difference between a common voltage applied from the common power line **172** to the driving thin film transistor **20** and a data voltage transferred from the switching thin film transistor **10** is stored in the capacitor **80**. The current corresponding to the stored voltage in the capacitor **80** flows to the organic light emitting diode **70** through the driving thin film transistor **20** so that the organic light emitting diode **70** emits light.

Hereinafter, a structure of an organic light emitting diode (OLED) display according to the first exemplary embodiment of the present invention will be described along a stacking order with reference to FIG. 3.

Also, a structure of a thin film transistor will be hereinafter described based on a driving thin film transistor **20**. A switching thin film transistor **10** will also be briefly described based on a difference from the driving thin film transistor.

The display substrate **110** will be firstly described. A first substrate member **111** is an insulating substrate made of glass, quartz, ceramic, or plastic. However, aspects of the present invention are not limited thereto. Therefore, the first substrate member **111** may be a metallic substrate made of stainless steel.

A buffer layer **120** is formed over the first substrate member **111**. The buffer layer **120** may be made of various materials that prevent impurity penetration and provide a level a surface thereof. For example, one of a silicon nitride layer

(SiNx), a silicon oxide layer (SiO₂), and a silicon oxynitride layer (SiOxNy) is used as the buffer layer **120**. However, since the buffer layer **120** is not an essential element, the buffer layer **120** may be omitted according to a type of substrate member **111** and a fabrication process condition.

The driving semiconductor layer **132** is formed over the buffer layer **120**. The driving semiconductor layer **132** is formed as a polysilicon layer. Also, the driving semiconductor layer **132** includes a channel area **135**, a source area **136**, and a drain area **137**. The source area **136** and the drain area **137** are disposed at both sides of the channel area **135**. The channel area is not doped with an impurity, and the source area **136** and the drain area **137** are doped with a P-type impurity (p+). Here, the doped ion material is a P-type impurity such as boron (B). Generally, B₂H₆ is used. However, such an impurity may vary according to a type of a thin film transistor.

Although a thin film transistor having a PMOS structure using a P-type impurity is used as the driving thin film transistor **20** in the first exemplary embodiment of the present invention, aspects of the present invention are not limited thereto. Therefore, both of a thin film transistor having an NMOS structure and a thin film transistor having a PMOS structure can be used as the driving thin film transistor **20**.

Although the driving thin film transistor **20** shown in FIG. 2 is a polycrystalline thin film transistor having a polysilicon layer, a switching thin film transistor **10** (not shown in FIG. 2) may be a polycrystal thin film transistor or an amorphous thin film transistor having an amorphous silicon layer.

A gate insulating layer **140** made of a silicon nitride (SiNx) or a silicon oxide (SiO₂) is formed over the driving semiconductor layer **132**. A gate wire having the driving gate electrode **155** is formed over the gate insulating layer **140**. Also, the gate wire further includes the gate line **151**, the first capacitor plate **158**, and other wires. The driving gate electrode **155** overlaps with at least a part of the driving semiconductor layer **132** and, particularly, overlaps with the channel area **135**.

An interlayer insulating layer **160** is formed over the gate insulating layer **140**, and the interlayer insulating layer **160** covers the driving gate electrode **155**. The gate insulating layer **140** and the interlayer insulating layer **160** commonly include through-holes to expose the source region **136** and the drain region **137** of the driving semiconductor layer **132**. The interlayer insulating layer **160** is made of a ceramic material such as silicon nitride (SiNx) or silicon oxide (SiO₂), like the gate insulating layer **140**.

A data wire is formed over the interlayer insulating layer **160**. The data wire includes the driving source electrode **176** and the driving drain electrode **177**. The data wire further includes the data line **171**, the common power line **172**, the second capacitor plate **178**, and other wires. The driving source electrode **176** and the driving drain electrode **177** are respectively connected to the source region **136** and the drain region **137** of the driving semiconductor layer **132** through through-holes formed in the interlayer insulating layer **160** and the gate insulating layer **140**.

As described above, the driving thin film transistor **20** is formed including the driving semiconductor layer **132**, the driving gate electrode **155**, the driving source electrode **176**, and the driving drain electrode **177**. However, the structure of the driving thin film transistor **20** according to aspects of the present invention is not limited thereto. The structure of the driving thin film transistor **20** may be modified into various well-known structures that can be conveniently embodied by those skilled in the art.

Over the interlayer insulating layer **160**, the planarization layer **180** is formed to cover the data wires **172**, **176**, **177**, and **178**. The planarization layer **180** removes steps and levels the surface to improve the luminous efficiency of the organic light emitting element **70**. Also, the planarization layer **180** has a contact hole **182** to expose a part of the drain electrode **177**.

The planarization layer **180** may be made of at least one of polyacrylate resins, epoxy resins, phenolic resins, polyamide resins, polyimide resins, unsaturated polyesters resins, polyphenylenether resins, polyphenylenesulfide resins, and benzocyclobutene (BCB).

Also, the first exemplary embodiment of the present invention is not limited to the above-described structure. One of the planarization layer **180** and the interlayer insulating layer **160** may be omitted.

A first pixel electrode **710** of the organic light emitting element **70** is formed over the planarization layer **180**. That is, the organic light emitting diode (OLED) display **100** includes a plurality of the first electrodes **710** disposed at each of a plurality of pixels. The plurality of first electrodes **710** is disposed at a predetermined distance. The first electrodes **710** are connected to the drain electrode **177** through the electrode contact hole **182** of the planarization layer **180**.

Also, the pixel defining layer **190** is formed over the planarization layer **180**. The pixel defining layer **190** has an opening that exposes the pixel electrode **710**. That is, the pixel defining layer **190** includes a plurality of openings formed at each of the pixels. The first electrode **710** is disposed corresponding to the opening of the pixel defining layer **190**. However, it is not essential to dispose the first electrode **710** at the opening of the pixel defining layer **190**. The first electrode **710** may be disposed under the pixel defining layer **190** to have a part overlapping with the pixel defining layer **190**. The pixel defining layer **190** may be made of a resin such as acryl-based polyacrylates or polyimides, or a silica-type mineral.

An organic emission layer **720** is formed over the first electrode **710**, and the second electrode **730** is formed over the organic emission layer **720**. As described above, the organic light emitting diode **70** is formed having the first electrode **710**, the organic emission layer **720**, and the second electrode **730**.

The organic emission layer **720** is made of a low molecular organic material or a high molecular organic material. The organic emission layer **720** is formed having multiple layers including a hole injection layer (HIL), a hole transport layer (HTL), an electron transport layer (ETL), and an electron injection layer (EIL). With regards to the organic emission layer **720** including all of the layers, the hole injection layer (HIL) is formed over the first electrode **710** which is an anode, the hole transport layer (HTL) is formed over the hole injection layer HIL, and the emission layer, the electron transport layer (ETL), and the electron injection layer (EIL) are sequentially stacked.

Although the organic emission layer **720** is disposed within the opening of the pixel defining layer **190**, the first exemplary embodiment of the present invention is not limited thereto. Therefore, the organic emission layer **720** may be formed not only over the first electrode **710** in the opening of the pixel defining layer **190** but also between the pixel defining layer **190** and the second electrode **730**. In more detail, the organic emission layer **720** may further include the hole injection layer (HIL), the hole transport layer (HTL), the electron transport layer (ETL), and the electron injection layer (EIL) with the emission layer. Excluding the emission layer, the hole injection layer (HIL), the hole transport layer (HTL), the

electron transport layer (ETL), and the electron injection layer (EIL) may be formed not only over the first electrode **710** but also over the pixel defining layer **190** using an open mask. That is, at least one of the layers included in the organic emission layer **720** may be disposed between the pixel defining layer **190** and the second electrode **730**.

The first electrode **710** and the second electrode **730** may be made of a transparent conductive material, a translucent conductive material, or a reflective conductive material. The type of the OLED display **100** is determined according to a type of material used to form the first electrode **710** and the second electrode **730**, wherein the type is a top emission type, a bottom emission type, or a dual emission type.

As the transparent conductive material, indium tin oxide (ITO), indium zinc oxide (IZO), zinc oxide (ZnO), or indium oxide (In₂O₃) may be used. As the reflective material and the translucent material, lithium (Li), calcium (Ca), lithium/calcium fluoride (LiF/Ca), lithium/aluminum fluoride (LiF/Al), aluminum (Al), silver (Ag), magnesium (Mg), or gold (Au) may be used.

A sealing member **210** is arranged opposite to and over the second electrode **730**. The sealing member **210** is made of transparent material such as glass or plastic. The sealing member **210** coheres with the display substrate **110** through the sealant **350** (see FIG. 1) formed along the edge.

Hereinafter, an internal structure of an organic light emitting diode (OLED) display **100** will be described based on a contact region **1595** of the first conductive wire **159** with reference to FIG. 4 and FIG. 5.

As shown in FIG. 4 and FIG. 5, a buffer layer **120** is formed over the substrate member **111**. A fill-up layer **139** is formed over the buffer layer **120**. Here, the fill-up layer **139** is formed only at a region corresponding to the contact region **1595** of the first conductive wire **159**. Also, the fill-up layer **139** is formed in the same layer of the semiconductor layer **320** of the thin film transistor **20** formed in the display area (DA) using the same material, that is, the fill-up layer **139** is formed without an additional process.

A gate insulating layer **140** is formed over the buffer layer **120** and the fill-up layer **139**. The first conductive wire **159** is formed over the gate insulating layer **140**. The first conductive wire **159** is formed of the same material of the gate electrode **155**, the gate line **151**, and the first capacitor plate **158** through the same manufacturing process. The first conductive wire **159** includes at least one of metals such as chromium (Cr), molybdenum (Mo), titanium (Ti), and tantalum (Ta).

The first conductive wire **159** includes a contact region **1595**. Also, the first conductive wire **159** is broken at regular intervals. Here, one end of broken first conductive wire **159** becomes the contact region **1595**.

An interlayer insulating layer **160** is formed over the first conductive wire **159**. The interlayer insulating layer **160** includes a plurality of wire contact holes exposing a part of the contact region **1595** of the first conductive wire **159**. Here, a thickness **t1** of the interlayer insulating layer **160** over the contact region **1595** having a plurality of wire contact holes **165** is thinner than the average thickness of the interlayer insulating layer **160**. This is because the interlayer insulating layer **160** around the wire contact holes **165** is partially etched while the plurality of wire contact holes **165** are formed. Therefore, the thickness **t1** of the interlayer insulating layer **160** formed over the contact region **1595** is different from a thickness **t2** of the interlayer insulating layer **160** not formed over the contact region **1595**. Here, the fill-up layer **139** is formed under the contact region **1595** to supplement the interlayer insulating layer **160** over the contact region **1595** at which location the interlayer insulating layer **160** has a com-

paratively thinner thickness **t1**. That is, the fill-up layer **139** suppresses a great step from forming by a thickness difference of the interlayer insulating layer **160**.

A second conductive wire **179** is formed over the interlayer insulating layer **160**. The second conductive wire **179** is connected to the first conductive wire **159** through the wire contact hole **165** of the interlayer insulating layer **160**.

A sealant **350** is formed over the second conductive wire **179**, and a sealing member **210** is attached on the sealant **350**. Also, the sealant **350** is made of ceramic material. For example, the sealant **350** may be made of frit. In more detail, the sealant **350** includes one side contacting the sealing member **210** and the other side contacting the second conductive wire **179** and a part of the interlayer insulating layer **160** where the second conductive wire **179** is not formed. Accordingly, the sealant **350** makes the sealing member **210** cohere with the display substrate **110**.

As described above, the second conductive wire **179** contacting the sealant **350** is formed to be comparatively flat without a large step-up due to the presence of the fill-up layer **139** disposed below. Therefore, the fill-up layer **139** prevents the adherence of the sealant **350** from deteriorating due to a step difference caused by the thickness change of an underlying insulating layer in the vicinity of the contact region. Accordingly, the strength of the OLED display **100** can be improved by suppressing the sealing member **210** from coming off from the display substrate **110**.

Hereinafter, an organic light emitting diode (OLED) display **200** according to the second exemplary embodiment of the present invention will be described with reference to FIG. 6.

As shown in FIG. 6, the OLED display **200** according to the second exemplary embodiment of the present invention includes a fill-up layer **189** disposed over a contact region **1595** of a first conductive wire **159**.

In more detail, the fill-up layer **189** is disposed between the second conductive wire **179** and the sealant **350**. Here, the fill-up layer **189** is formed only at a region corresponding to the contact region **1595** of the first conductive wire **159**. Also, the fill-up layer **189** is formed of the same material of a planarization layer **180** formed in a display area (DA) through the same manufacturing process.

Further, a thickness **t1** of the interlayer insulating layer **160** formed over the contact region **1595** is thinner than a thickness **t2** of the interlayer insulating layer **160** not formed over the contact region **1595**.

As described above, the fill-up layer **189** supplements the interlayer insulating layer **160** over the contact region **1595** that has the comparatively thinner thickness **t1**. That is, the fill-up layer **189** fills up a step formed by a thickness difference of the interlayer insulating layer **160**. That is, the second conductive wire **179** contacting the sealant **350** and the fill-up layer **189** are formed to be comparatively flat without a step. Accordingly, adherence of the sealant **350** is prevented from deterioration caused by a step. Therefore, the strength of the OLED display **200** is improved by suppressing the sealing member **210** from coming off from the display substrate **110**.

Hereinafter, an organic light emitting diode (OLED) display **300** according to the third exemplary embodiment of the present invention will be described with reference to FIG. 7.

As shown in FIG. 7, the OLED display **300** according to the third exemplary embodiment of the present invention includes a fill-up layer **719** that is disposed over a contact region **1595** of a first conductive wire **159**.

In more detail, the fill-up layer **719** is disposed between a second conductive wire **179** and a sealant **350**. Here, the fill-up layer **719** is formed only at a region corresponding to

the contact region **1595** of the first conductive wire **159**. Also, the fill-up layer **719** is formed of the same material of the first electrode **710** of the OLED **70** formed in a display area (DA) through the same manufacturing process.

Also, a thickness **t1** of an interlayer insulating layer **160** formed over the contact region **1595** is thinner than a thickness **t2** of the interlayer insulating layer **160**.

As described above, the fill-up layer **719** supplements the interlayer insulating layer **160** formed over the contact region **1595** that has a comparatively thinner thickness **t1**. That is, the fill-up layer **719** fills up a step formed by a thickness difference of the interlayer insulating layer **160**. In other words, the second conductive wire **179** contacting the sealant **350** and the fill-up layer **719** are formed to be comparatively flat without a great step. Accordingly, it prevents the adherence of the sealant **350** from deterioration due to the step difference. Therefore, the strength of the OLED display **300** is improved by suppressing the sealing member **210** from coming off from the display substrate **110**.

Although a few embodiments of the present invention have been shown and described, it would be appreciated by those skilled in the art that changes may be made in this embodiment without departing from the principles and spirit of the invention, the scope of which is defined in the claims and their equivalents.

What is claimed is:

1. An organic light emitting diode (OLED) display device, comprising:

- a first substrate member;
- a first conductive wire having a contact region and formed over the first substrate member;
- an insulating layer including a plurality of wire contact holes exposing a part of the contact region of the first conductive wire and formed over the first conductive wire;
- a second conductive wire formed over the first conductive wire and connected to the first conductive wire through the plurality of wire contact holes of the insulating layer;
- a sealant formed over the second conductive wire;
- a sealing member formed over the sealant; and
- a fill-up layer disposed over the first conductive wire, the sealant being comprised of frit and including one side that contacts the sealing member and another side that contacts a substantially flat structure.

2. The OLED display device of claim 1, wherein the insulating layer disposed over the contact region having the plurality of wire contact holes is thinner than an average thickness of the insulating layer.

3. The OLED display device of claim 2, wherein the first conductive wire is broken at regular intervals.

4. The OLED display device of claim 3, wherein the first conductive wire includes at least one metal of chromium (Cr), molybdenum (Mo), titanium (Ti), and tantalum (Ta).

5. The OLED display device of claim 2, wherein the first conductive wire and the second conductive wire are formed to be flat.

6. The OLED display device of claim 1, further comprising a thin film transistor, an organic light emitting diode, and a planarization layer disposed between the thin film transistor and the organic light emitting diode, wherein the fill-up layer is formed of the same material as that of the planarization layer through the same manufacturing process.

7. The OLED display device of claim 1, further comprising an organic light emitting diode having a first electrode, an organic emission layer formed over the first electrode, and a second electrode formed over the organic emission layer, wherein the fill-up layer is formed of the same material as that

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of the first electrode of the organic light emitting diode through the same manufacturing process.

8. The OLED display device of claim 3, comprised of the regular intervals of the first conductive wire terminating at one of a plurality of contact regions, the regular intervals being electrically connected to each other by a second conductive wire.

9. An organic light emitting diode (OLED) display device, comprising:

- a first substrate member;
- a buffer layer arranged over the first substrate;
- a first conductive wire having a contact region and arranged over the first substrate member;
- an insulating layer including a plurality of wire contact holes exposing a part of the contact region of the first conductive wire and arranged over the first conductive wire;
- a second conductive wire arranged over the first conductive wire and connected to the first conductive wire through the plurality of wire contact holes of the insulating layer;
- a sealant arranged over the second conductive wire;
- a sealing member arranged over the sealant; and
- a fill-up layer arranged on the buffer layer and disposed over the first conductive wire, wherein the insulating layer disposed over the contact region having the plurality of wire contact holes has a first thickness t_1 that is greater than zero but less than a second thickness t_2 of the insulating layer external to the contact region, and wherein the fill-up layer is only within the contact region.

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10. The OLED display device of claim 9, comprised of the first conductive wire and the second conductive wire being used for image quality test and an aging process during a fabrication of the OLED display and are not elements for driving the OLED display.

11. The OLED display device of claim 9, comprised of the fill-up layer being arranged between the second conductive wire and the sealant.

12. The OLED display device of claim 11, comprised of the fill-up layer being comprised of a material selected from a group consisting of a polyacrylate resin, an epoxy resins, a phenolic resin, a polyamide resin, a polyimide resin, an unsaturated polyesters resin, a polyphenylenether resin, a polyphenylenesulfide resin, and benzocyclobutene (BCB).

13. The OLED display device of claim 11, comprised of the fill-up layer being comprised of a material selected from a group consisting of indium tin oxide (ITO), indium zinc oxide (IZO), zinc oxide (ZnO), or indium oxide (In_2O_3), lithium (Li), calcium (Ca), lithium/calcium fluoride (LiF/Ca), lithium/aluminum fluoride (LiF/Al), aluminum (Al), silver (Ag), magnesium (Mg) and gold (Au).

14. The OLED display device of claim 1, comprised of the sealant being comprised of frit and including one side that contacts the sealing member and another side that contacts a substantially flat structure caused by the fill-up layer canceling out the step difference of the insulating layer.

* * * * *

专利名称(译)	有机发光二极管显示器通过防止密封剂的剥落而具有改善的强度		
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[标]申请(专利权)人(译)	三星显示有限公司		
申请(专利权)人(译)	三星DISPLAY CO. , LTD.		
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摘要(译)

有机发光二极管 (OLED) 显示器。 OLED显示器包括第一基板构件，具有接触区域并形成在第一基板构件上的第一导线，绝缘层包括多个线接触孔，所述多个线接触孔暴露第一导线的接触区域的一部分并形成在第一导线，第二导线，形成在第一导线上并通过绝缘层的多个导线接触孔连接到第一导线，密封剂形成在第二导线上，密封构件形成在密封剂上方以及设置在第一导线的接触区域之上或之下的填充层。

